

SANYO Semiconductors DATA SHEET

N-Channel Silicon MOSFET

MCH6406 — General-Purpose Switching Device **Applications**

Features

- · Low ON-resistance.
- 4V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		30	٧
Gate-to-Source Voltage	VGSS		±20	٧
Drain Current (DC)	ID		5	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	20	Α
Allowable Power Dissipation	PD	Mounted on a ceramic board (900mm ² X0.8mm)	1.5	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Llait
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	30			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =30V, V _{GS} =0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	VGS= ±16V, VDS=0V			±10	μΑ
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =1mA	1.2		2.6	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =2.5A	2.8	4		S
Static Drain-to-Source On-State Resistance	RDS(on)1	ID=2.5A, VGS=10V		37	48	mΩ
	R _{DS} (on)2	I _D =1.2A, V _{GS} =4V		63	88	mΩ
Input Capacitance	Ciss	V _{DS} =10V, f=1MHz		460		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		95		pF
Reverse Transfer Capacitance	Crss	V _{DS} =10V, f=1MHz		75		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		11		ns
Rise Time	t _r	See specified Test Circuit.		12		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		32		ns
Fall Time	tf	See specified Test Circuit.		18		ns

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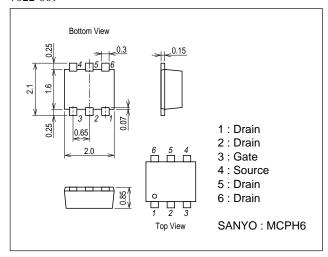
MCH6406

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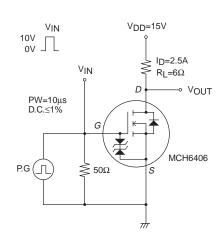
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Total Gate Charge	Qg	V _{DS} =10V, V _{GS} =10V, I _D =5A		8.5		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =10V, I _D =5A		1.8		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =10V, V _{GS} =10V, I _D =5A		1.3		nC
Diode Forward Voltage	VSD	IS=5A, VGS=0V		0.86	1.2	V

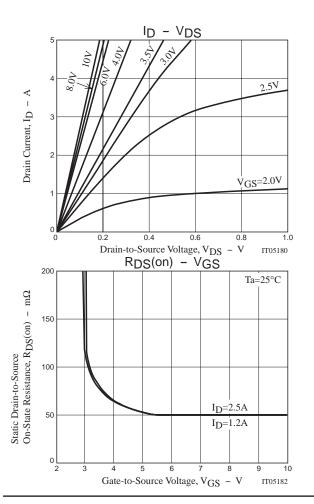
Package Dimensions

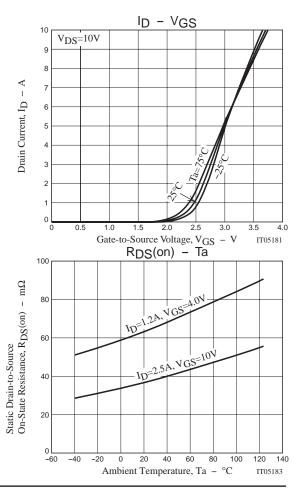
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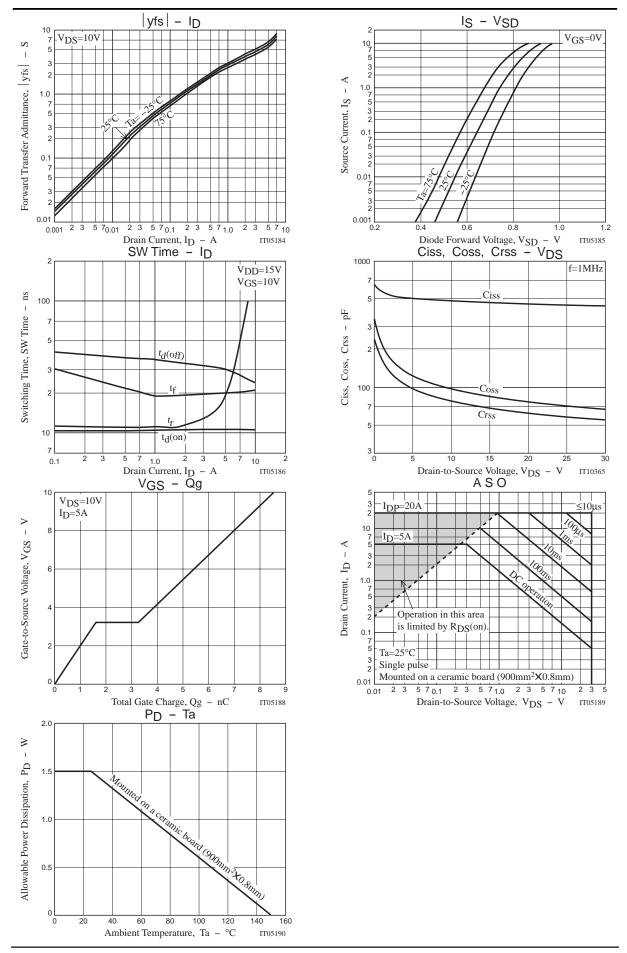


Switching Time Test Circuit









Note on usage: Since the MCH6406 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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